September 2001

FDC634P

# P-Channel 2.5V Specified PowerTrench<sup>®</sup> MOSFET

### **General Description**

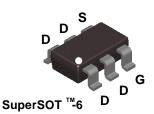
This P-Channel 2.5V specified MOSFET uses Fairchild's low voltage PowerTrench process. It has been optimized for battery power management applications.

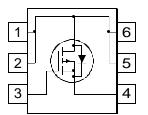
### Applications

- Battery management
- · Load switch
- Battery protection

## Features

- -3.5 A, -20 V.  $R_{DS(ON)} = 80 \text{ m}\Omega @ V_{GS} = -4.5 \text{ V}$  $R_{DS(ON)} = 110 \text{ m}\Omega @ V_{GS} = -2.5 \text{ V}$
- Low gate charge (7.2 nC typical)
- High performance trench technology for extremely low R<sub>DS(ON)</sub>





# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-20	V
V <sub>GSS</sub>	Gate-Source Voltage		±8	V
l <sub>D</sub>	Drain Current – Continuous	(Note 1a)	-3.5	A
	- Pulsed		-20	
PD	Maximum Power Dissipation	(Note 1a)	1.6	W
		(Note 1b)	0.8	
$T_J, T_{STG}$	Operating and Storage Junction Temperat	ture Range	-55 to +150	°C

# Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	30	°C/W

# **Package Marking and Ordering Information**

Device Marking	Device	Reel Size	Tape width	Quantity
.634	FDC634P	7"	8mm	3000 units

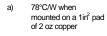
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FDC634P

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV <sub>DSS</sub>	Drain–Source Breakdown Voltage	$V_{GS} = 0 V, I_D = -250 \mu A$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		-12		mV/⁰C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -16 V$ , $V_{GS} = 0 V$			-1	μA
GSSF	Gate-Body Leakage, Forward	$V_{GS} = 8 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage, Reverse	$V_{GS} = -8 V$ $V_{DS} = 0 V$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$	-0.4	-0.8	-1.5	V
<u>ΔVgs(th)</u> ΔTj	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		3		mV/ºC
R <sub>DS(on)</sub>	Static Drain–Source On–Resistance	$ \begin{array}{l} V_{GS} = -4.5 \ V,  b_{D} = -3.5 \ A \\ V_{GS} = -2.5 \ V,  b_{D} = -3.1 \ A \\ V_{GS} = -4.5 \ V, \ b_{D} = -3.5 A, T_{J} = 125^{\circ} C \end{array} $		60 82 77	80 110 130	mΩ
D(on)	On–State Drain Current	$V_{GS} = -4.5 \text{ V},  V_{DS} = -5 \text{ V}$	-10			А
<b>g</b> fs	Forward Transconductance	$V_{DS} = -5 V$ , $I_D = -3.5 A$		11		S
Dvnamic	Characteristics					
Ciss	Input Capacitance	$V_{DS} = -10 V$ , $V_{GS} = 0 V$ ,		779		pF
Coss	Output Capacitance	f = 1.0 MHz		121		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			56		pF
Switchin	g Characteristics (Note 2)	•				
t <sub>d(on)</sub>	Turn–On Delay Time	$V_{DD} = -10 V$ , $I_D = -1 A$ ,		10	20	ns
tr	Turn–On Rise Time	$V_{GS} = -4.5 \ V, \qquad R_{GEN} = 6 \ \Omega$		9	19	ns
t <sub>d(off)</sub>	Turn–Off Delay Time			27	43	ns
t <sub>f</sub>	Turn–Off Fall Time			11	20	ns
Qg	Total Gate Charge	$V_{DS} = -10 V$ , $I_D = -3.5 A$ ,		7.2	10	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -4.5 V$		1.7		nC
Q <sub>gd</sub>	Gate–Drain Charge			1.5		nC
Drain–So	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source	0			-1.3	Α
V <sub>SD</sub>	Drain–Source Diode Forward Voltage	$V_{GS} = 0 V$ , $I_S = -1.3 A$ (Note 2)		-0.8	-1.2	V

the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.





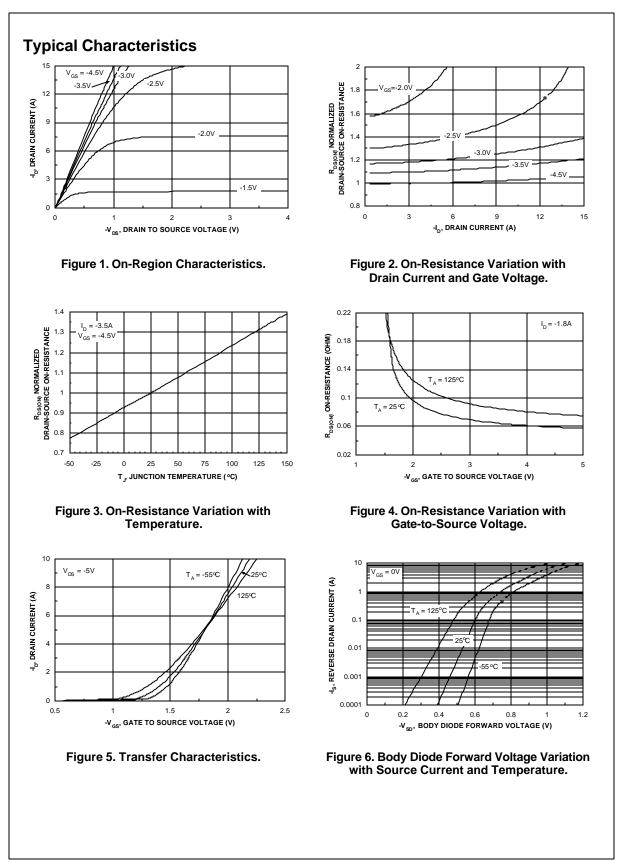


b) 156°C/W when mounted on a minimum pad of 2 oz copper

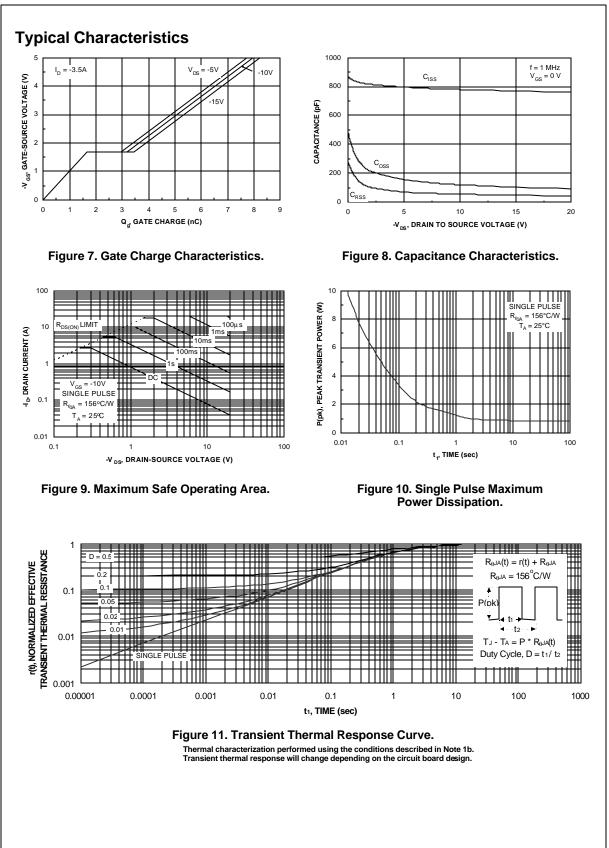
Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu s,$  Duty Cycle < 2.0%

FDC634P Rev E(W)



FDC634P



FDC634P

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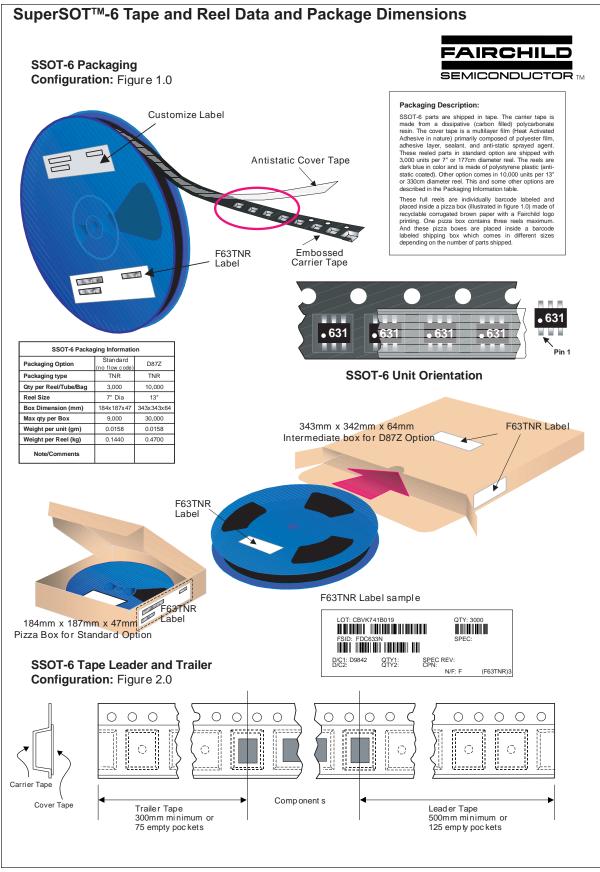
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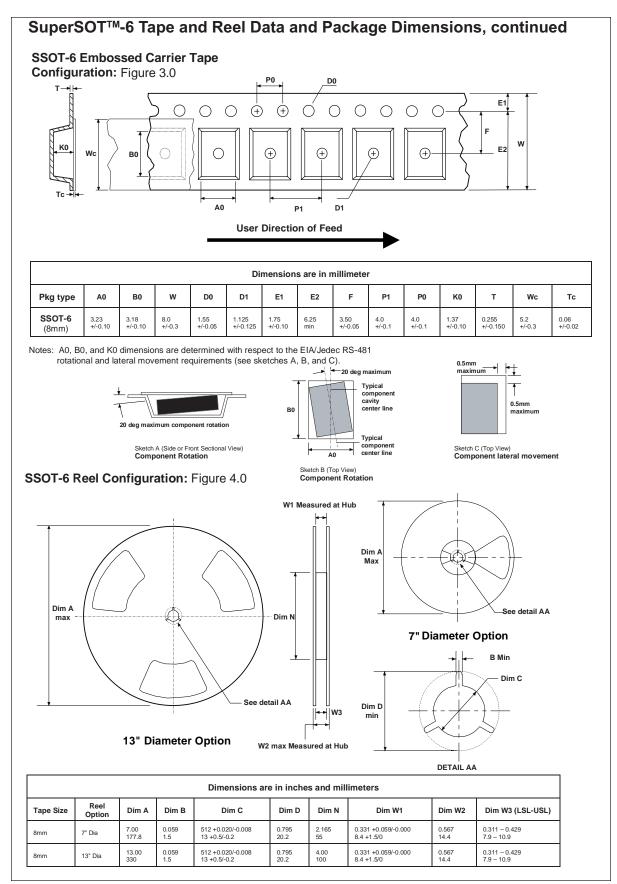
#### **PRODUCT STATUS DEFINITIONS**

**Definition of Terms** 

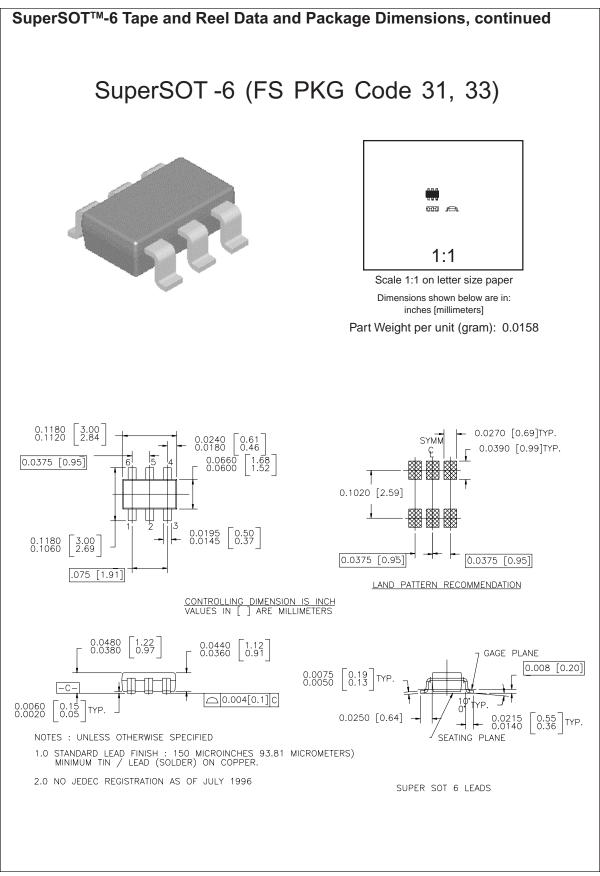
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August 1999, Rev. C



July 1999, Rev. C



September 1998, Rev. A